



JMD200KD18T2W

Diode Module

Features

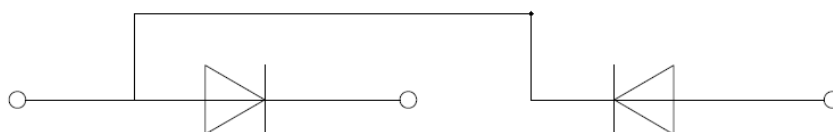
- A package of series of two diodes
- Heat transfer through alumina ceramic and metal substrate
- Welding by vacuum welding technology, which provide high reliability

Product Summary

Parameter	Value	Unit
V_{RRM}	1800	V
$I_{F(AV)}(@ T_C = 100^\circ\text{C})$	200	A
$I_{FSM}(@ t_p = 10\text{ms})$	5800	A
$V_F(\text{Max})$	1.60	V

Applications

- AC converter
- Inverter
- DC moto



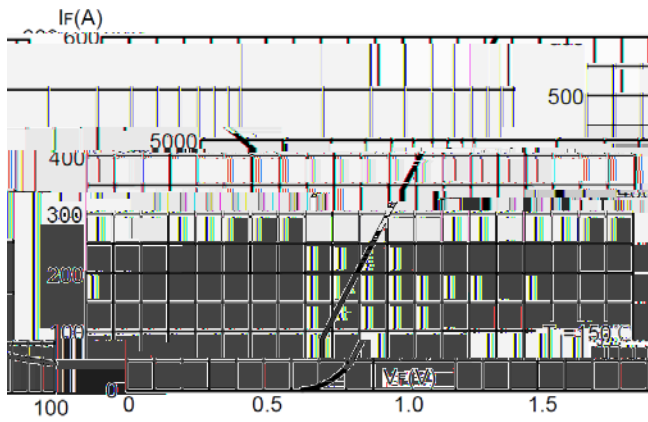
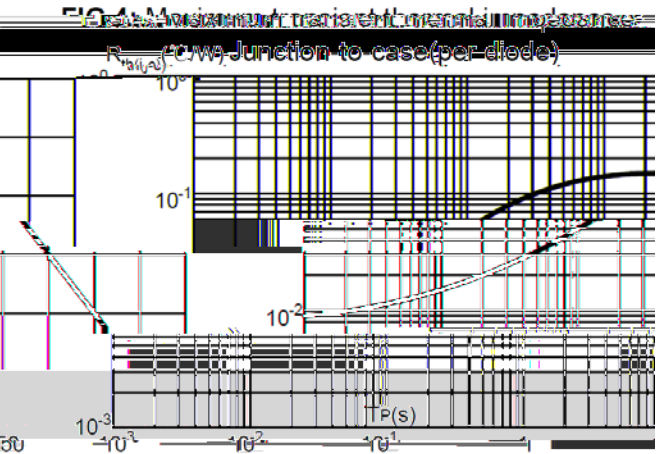
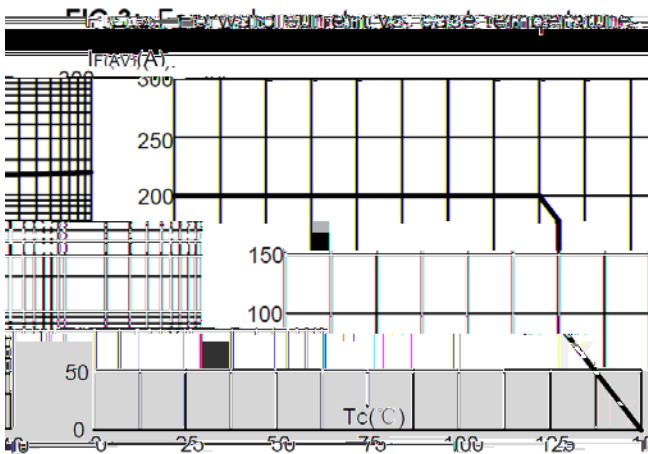
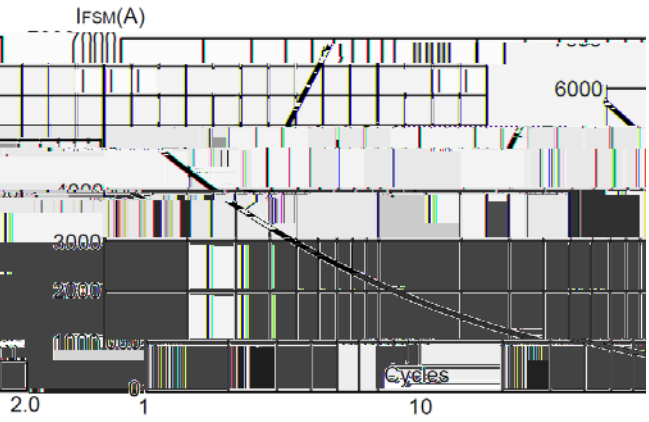
Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RRM}	1800	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	1900	V
Average forward current	$T_C = 100^\circ\text{C}$	$I_{F(AV)}$	200	A
Forward surge current	1/2 cycle, Sine wave, 50Hz	I_{FSM}	5800	A
I^2t value for fusing	$T_{vj} = 25$	I^2t	168200	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

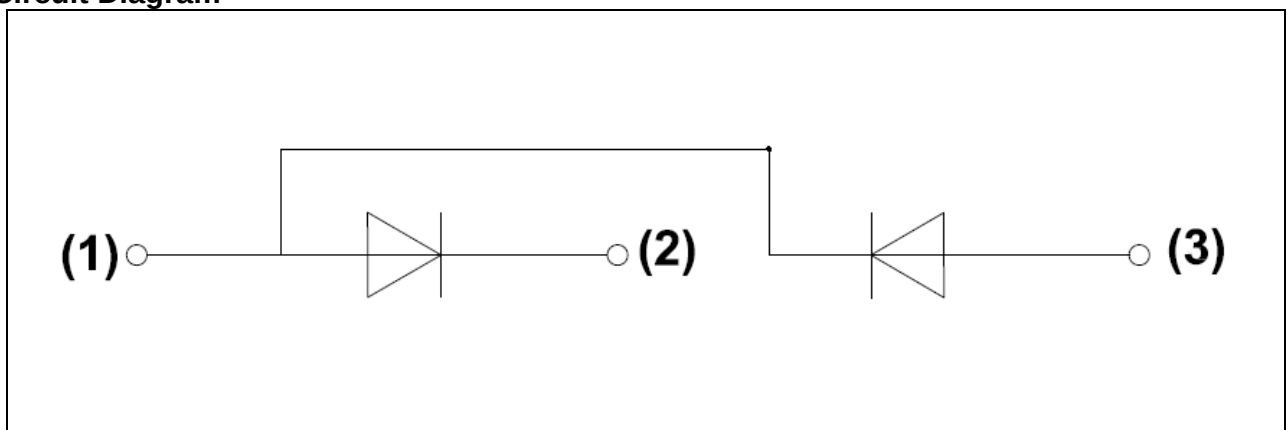
**Electrical Characteristics** (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

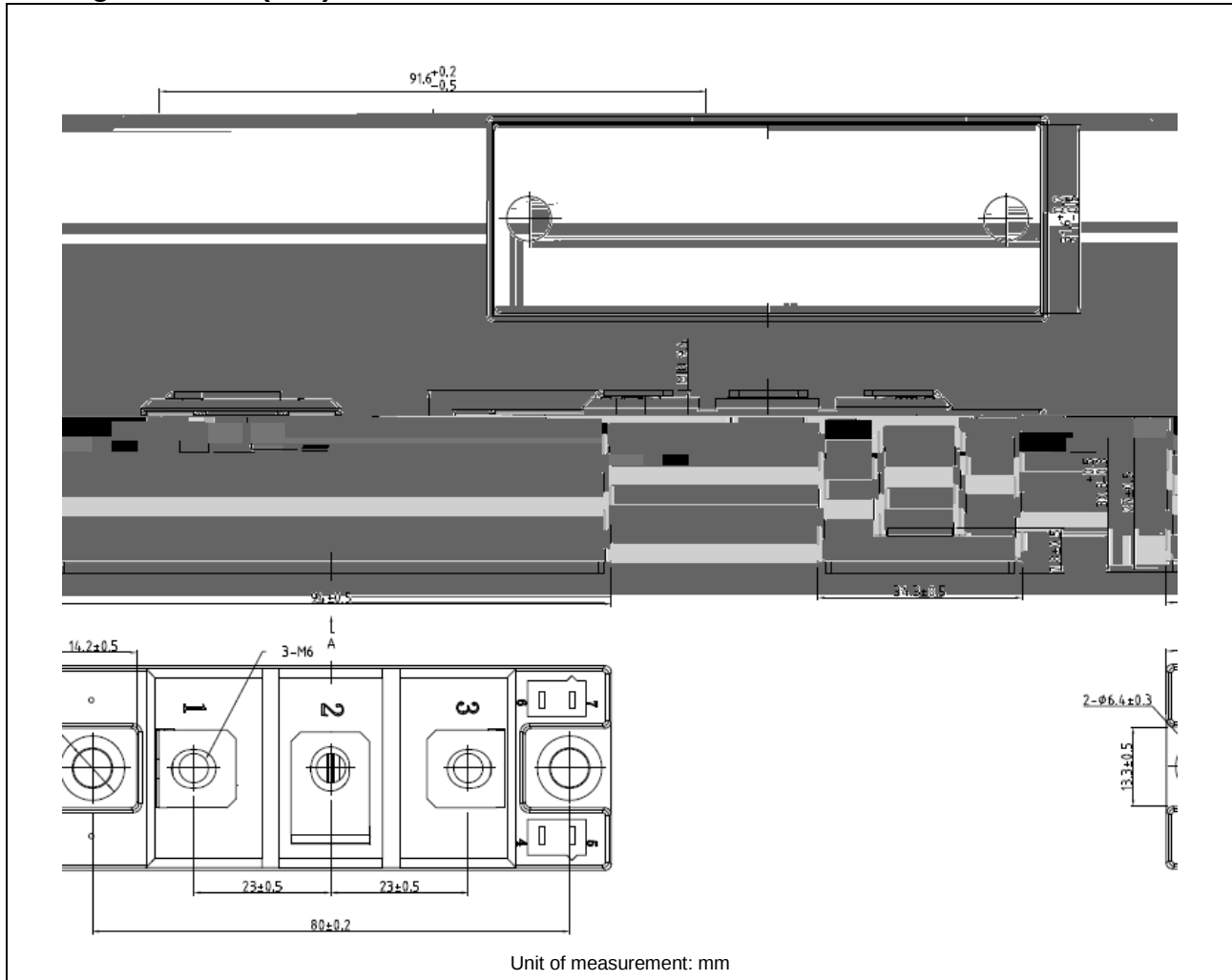
Parameter	Conditions	Symbol	Values	Unit

Typical Electrical & Thermal Characteristics

FIG.1: Forward characteristics(per diode)

FIG.2: Peak on-state surge current


Circuit Diagram



Package Outlines (mm)




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